# 2-W MONO AUDIO POWER AMPLIFIER WITH HEADPHONE DRIVE

SLOS276B - JANUARY 2000 - REVISED MARCH 2000

- Ideal for Notebook Computers, PDAs, and **Other Small Portable Audio Devices**
- 2 W Into 4- $\Omega$  From 5-V Supply
- 0.6 W Into 4- $\Omega$  From 3-V Supply
- **Stereo Head Phone Drive**
- Separate Inputs for the Mono (BTL) Signal, and Stereo (SE) Left/Right Signals
- Wide Power Supply Compatibility 2.5 V to 5.5 V
- **Low Supply Current** 
  - 4.2 mA Typical at 5 V
  - 3.6 mA Typical at 3 V
- Shutdown Control . . . 1 μA Typical
- Shutdown Pin is TTL Compatible
- -40°C to 85°C Operating Temperature
- Space-Saving, Thermally-Enhanced MSOP **Packaging**

#### **DGQ PACKAGE** (TOP VIEW) MONO-IN □ 10 LO/MO-SHUTDOWN I 9 LIN $V_{DD} \square$ □ GND BYPASS □ RIN 🗆 ☐ RO/MO+

### description

The TPA0213 is a 2-W mono bridge-tied-load (BTL) amplifier designed to drive speakers with as low as 4- $\Omega$ impedance. The amplifier can be reconfigured on-the-fly to drive two stereo single-ended (SE) signals into head phones. This makes the device ideal for use in small notebook computers, PDAs, Digital Personal Audio players, anyplace a mono speaker and stereo head phones are required. From a 5-V supply, the TPA0213 can deliver 2-W of power into a  $4-\Omega$  speaker.

The gain of the input stage is set by the user-selected input resistor and a 50-k $\Omega$  internal feedback resistor  $(A_V = -R_F/R_I)$ . The power stage is internally configured with a gain of -1.25 V/V in SE mode, and -2.5 V/V in BTL mode. Thus, the overall gain of the amplifier is 62.5 k $\Omega$ / R<sub>I</sub> in SE mode and 125 k $\Omega$ / R<sub>I</sub> in BTL mode.

The TPA0213 is available in the 10-pin thermally-enhanced MSOP package (DGQ) and operates over an ambient temperature range of -40°C to 85°C.

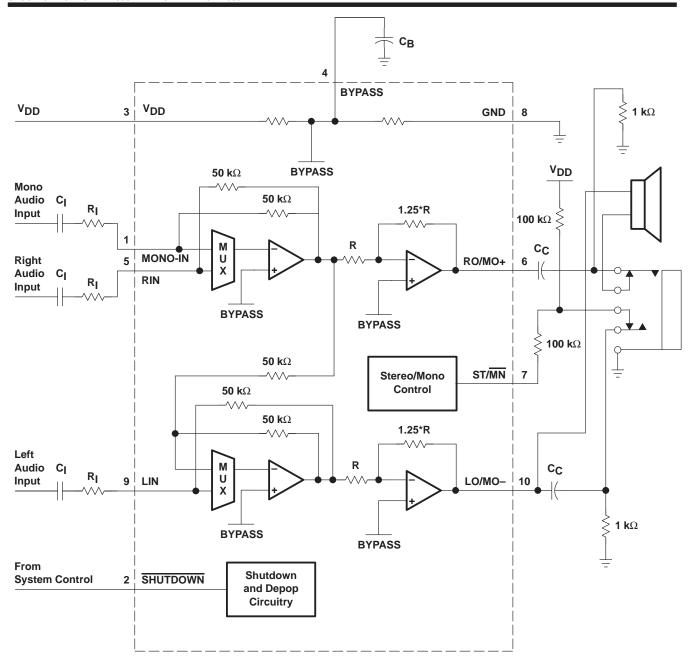


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#### **AVAILABLE OPTIONS**

	PACKAGED DEVICES	MSOP
TA	MSOP† (DGQ)	SYMBOLIZATION
-40°C to 85°C	TPA0213DGQ	AEH

<sup>†</sup> The DGQ package are available taped and reeled. To order a taped and reeled part, add the suffix R to the part number (e.g., TPA0213DGQR).

### **Terminal Functions**

TERMINA	\L	1/0	DECORPORTION
NAME	NO.	1/0	DESCRIPTION
MONO-IN	1	- 1	Mono input terminal
SHUTDOWN	2	- 1	SHUTDOWN places the entire device in shutdown mode when held low. TTL compatible input.
$V_{DD}$	3	1	V <sub>DD</sub> is the supply voltage terminal.
BYPASS	4	I	BYPASS is the tap to the voltage divider for internal mid-supply bias. This terminal should be connected to a $0.1$ - $\mu$ F to $1$ - $\mu$ F capacitor.
RIN	5	- 1	Right-channel input terminal
RO/MO+	6	0	Right-output in SE mode and mono positive output in BTL mode
ST/MN	7	I	Selects between stereo and mono mode. When held high, the amplifier is in SE stereo mode, while held low, the amplifier is in BTL mono mode.
GND	8		Ground terminal
LIN	9	I	Left-channel input terminal
LO/MO-	10	0	Left-output in SE mode and mono negative output in BTL mode.

## absolute maximum ratings over operating free-air temperature range (unless otherwise noted)§

Supply voltage, V <sub>DD</sub>	6 V
Input voltage, V <sub>I</sub>	
Continuous total power dissipation	internally limited (see Dissipation Rating Table)
Operating free-air temperature range, T <sub>A</sub> (see Table 3)	–40°C to 85°C
Operating junction temperature range, T <sub>J</sub>	–40°C to 150°C
Storage temperature range, T <sub>stq</sub>	–65°C to 150°C
Lead temperature 1.6 mm (1/16 inch) from case for 10 secon	ds 260°C

<sup>§</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

### **DISSIPATION RATING TABLE**

PACKAGE	$T_{\mbox{A}} \le 25^{\circ}\mbox{C}$	DERATING FACTOR	T <sub>A</sub> = 70°C	T <sub>A</sub> = 85°C
DGQ	2.14 W¶	17.1 mW/°C	1.37 W	1.11 W

<sup>¶</sup> Please see the Texas Instruments document, PowerPAD Thermally Enhanced Package Application Report (literature number SLMA002), for more information on the PowerPAD package. The thermal data was measured on a PCB layout based on the information in the section entitled Texas Instruments Recommended Board for PowerPAD on page 33 of the before mentioned document.



# **TPA0213** 2-W MONO AUDIO POWER AMPLIFIER WITH HEADPHONE DRIVE

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### recommended operating conditions

			MIN	MAX	UNIT
Supply voltage, V <sub>DD</sub>			2.5	5.5	V
High-level input voltage, VIH	OT/MAN	V <sub>DD</sub> = 3 V	2.7		
	ST/MN	V <sub>DD</sub> = 5 V	4.5		V
	SHUTDOWN	SHUTDOWN			
	ST/MN	V <sub>DD</sub> = 3 V		1.65	
Low-level input voltage, V <sub>IL</sub>		V <sub>DD</sub> = 5 V		2.75	V
	SHUTDOWN			0.8	
Operating free-air temperature, T <sub>A</sub>			-40	85	°C

### electrical characteristics at specified free-air temperature, $V_{DD}$ = 3 V, $T_A$ = 25°C (unless otherwise noted)

PARAMETER		TEST COND	MIN	TYP	MAX	UNIT	
IVool	Output offset voltage (measured differentially)	$V_{10} = 0,$	Gain = 8 dB			30	mV
PSRR	Power supply rejection ratio	$V_{DD} = 2.9 \text{ V to } 3.1 \text{ V},$	BTL mode		65		dB
IIIHI	High-level input current	$V_{DD} = 3.3 V,$	$V_I = V_{DD}$			1	μΑ
I <sub>I</sub> L	Low-level input current	$V_{DD} = 3.3 \text{ V},$	V <sub>I</sub> = 0			1	μΑ
Z <sub>l</sub>	Input impedance				50		kΩ
I <sub>DD</sub>	Supply current				3.6	5.5	mA
I <sub>DD(SD)</sub>	Supply current, shutdown mode				1	10	μΑ

# operating characteristics, $V_{DD}$ = 3 V, $T_A$ = 25°C, $R_L$ = 4 $\Omega$ , f = 1 kHz (unless otherwise noted)

	PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
D-	Output names and Note 4	THD = 1%,	BTL mode			660		mW
Po	Output power, see Note 1	THD = 0.1%,	SE mode,	$R_L = 32 \Omega$		33		mvv
THD + N	Total harmonic distortion plus noise	$P_0 = 500 \text{ mW},$	f = 20 Hz to 20 kHz			0.2%		
Вом	Maximum output power bandwidth	Gain = 8 dB,	THD = 2%			20		kHz
	Sunnle rinnle rejection ratio	f = 1 kHz.	CB = 0.47 μF	BTL mode		52		dB
	Su le II · le rejection ratio	1 = 1 KHZ,	1 KΠZ, CB = 0.47 μF			62		ub
Vn	Noise output voltage	00 0 47 5		BTL mode		42		
		$CB = 0.47 \mu F$ ,	f = 20 Hz to 20 kHz	SE mode		21		μVRMS

NOTE 1: Output power is measured at the output terminals of the device at f = 1 kHz.



### electrical characteristics at specified free-air temperature, $V_{DD}$ = 5 V, $T_A$ = 25°C (unless otherwise noted)

	PARAMETER	TEST COND	MIN	TYP	MAX	UNIT	
IVool	Output offset voltage (measured differentially)	V <sub>IO</sub> = 0,	Gain = 8 dB			30	mV
PSRR	Power supply rejection ratio	$V_{DD} = 4.9 \text{ V to } 5.1 \text{ V},$	BTL mode		62		dB
I <sub>IH</sub>	High-level input current	$V_{DD} = 5.5 V,$	$V_I = V_{DD}$			1	μΑ
I <sub>I</sub> L	Low-level input current	$V_{DD} = 5.5 V$ ,	V <sub>I</sub> = 0			1	μΑ
Z <sub>l</sub>	Input impedance				50		kΩ
I <sub>DD</sub>	Supply current				4.2	6.3	mA
I <sub>DD(SD)</sub>	Supply current, shutdown mode				1	10	μΑ

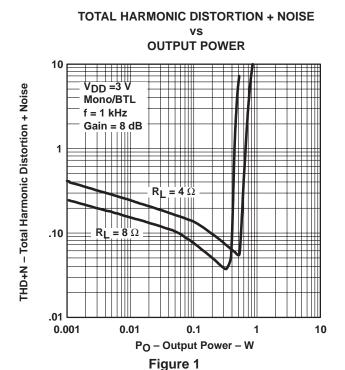
# operating characteristics, $\rm V_{DD}$ = 5 V, $\rm T_A$ = 25°C, $\rm R_L$ = 4 $\Omega$

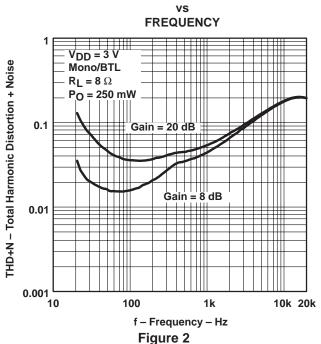
	PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
D <sub>o</sub>	Output power, see Note 1	THD = 0.3%,	BTL mode			2		W
Ро		THD = 0.1%,	SE mode,	$R_L = 32 \Omega$		90		mW
THD + N	Total harmonic distortion plus noise	P <sub>O</sub> = 1.5 W,	f = 20 Hz to 20 kHz			0.2%		
ВОМ	Maximum output power bandwidth	Gain = 6 dB,	THD = 2%			20		kHz
	Supply ripply rejection ratio	f = 1 kHz.	CB = 0.47 μF	BTL mode		52		dB
	Supple ripple rejection ratio	I = I KHZ,	CB = 0.47 μF	SE mode		62		uБ
V	$V_{\text{n}}$ Noise output voltage CB = 0.47 $\mu$ F, f = 20 Hz to 20	f = 20 Hz to 20 kHz	BTL mode		42		u\/5	
٧n		OB = 0.47 μr,	1 – 20 112 to 20 KHZ	SE mode		21		μVRMS

NOTE 1: Output power is measured at the output terminals of the device at f = 1 kHz.

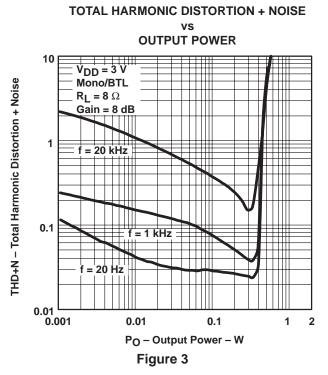


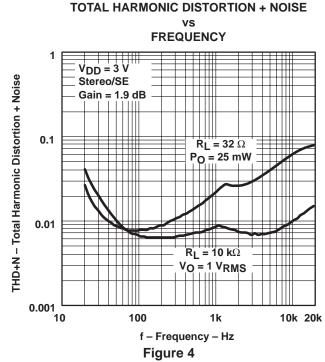
### TYPICAL CHARACTERISTICS





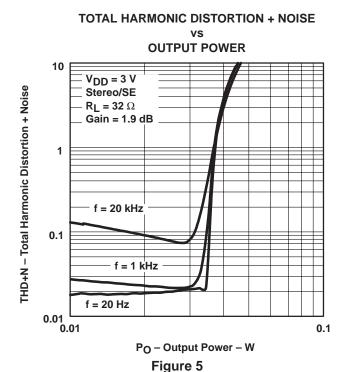
**TOTAL HARMONIC DISTORTION + NOISE** 

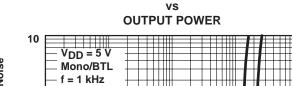


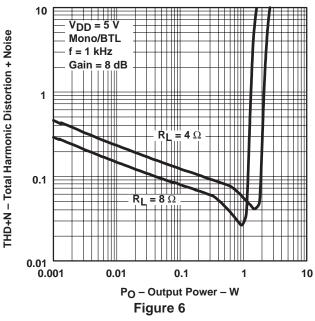


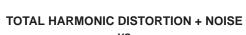
**TOTAL HARMONIC DISTORTION + NOISE** 

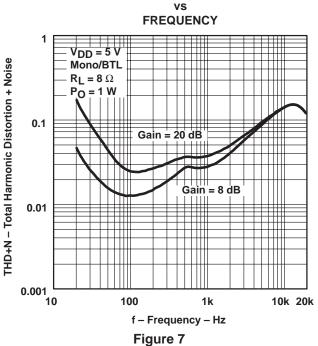
### TYPICAL CHARACTERISTICS



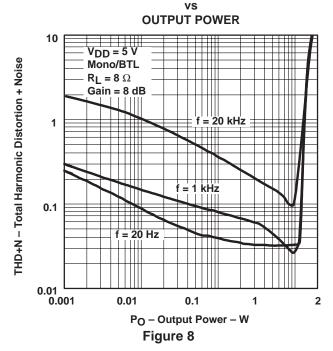




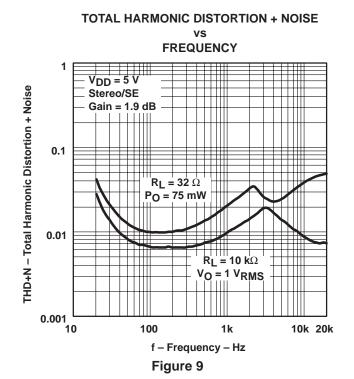


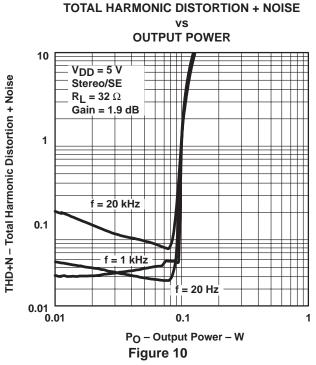


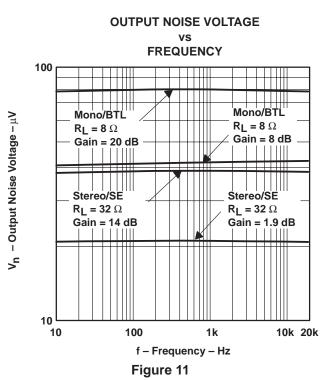
# **TOTAL HARMONIC DISTORTION + NOISE**

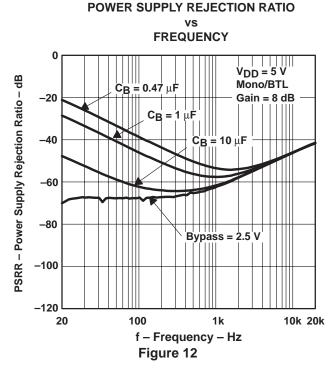


### **TYPICAL CHARACTERISTICS**









### **TYPICAL CHARACTERISTICS**

# **POWER SUPPLY REJECTION RATIO**

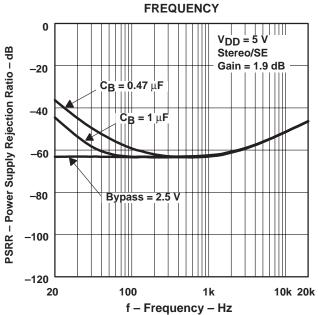


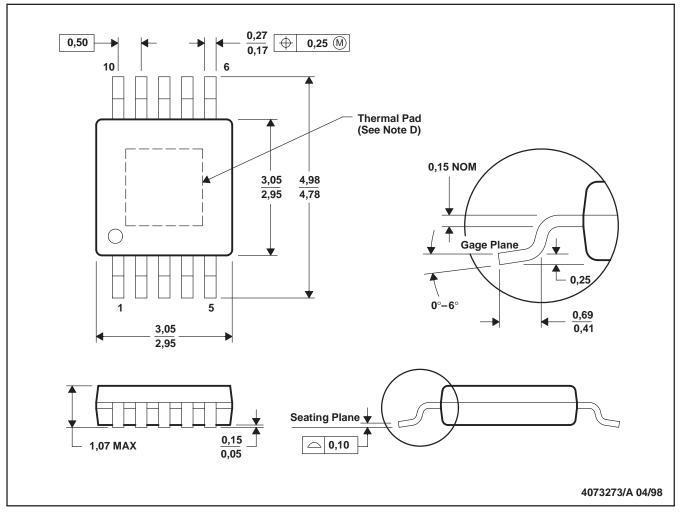
Figure 13

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### **MECHANICAL DATA**

### DGQ (S-PDSO-G10)

### PowerPAD™ PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion.
- The package thermal performance may be enhanced by bonding the thermal pad to an external thermal plane. This pad is electrically and thermally connected to the backside of the die and possibly selected leads. The dimension of the thermal pad is 1.40 mm (height as illustrated) × 1.80 (width as illustrated) mm (maximum). The pad is centered on the bottom of the package.

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